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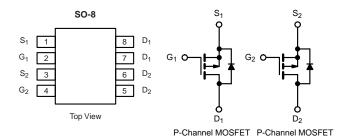
Dual P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.035			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.055			
I _D (A) per leg	-5.4			
Configuration	Dual			

FEATURES

- DT-Trench Power MOSFET
- AEC-Q101 Qualified^c
- \bullet 100 % R_{g} and UIS Tested





ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 30	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C	1	- 5.4		
	T _C = 125 °C	- I _D	- 3.8		
Continuous Source Current (Diode Conduction)		Is	- 3	Α	
Pulsed Drain Current ^a		I _{DM}	- 26		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 17		
Single Pulse Avalanche Energy	L = U.1 Min	E _{AS}	14	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	- P _D	3.3	W	
	T _C = 125 °C		1.1] vv	
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient PC	CB Mount ^b	R_{thJA}	110	°C/W		
Junction-to-Foot (Drain)		R _{thJF}	45	C/VV		

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					·	ı		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 30	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-	- 2.5] V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = - 30 V	-	-	- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 125 °C	-	-	- 50	μΑ	
		V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 175 °C	-	-	- 150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 20	-	-	Α	
		V _{GS} = - 10 V	I _D = - 4.9 A	-	0.035	0.050	Ω	
Dunin Course On Chata Basistanas	Б	V _{GS} = - 10 V	I _D = - 4.9 A, T _J = 125 °C	-	-	0.066		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 4.9 A, T _J = 175 °C	-	-	0.076		
		V _{GS} = - 4.5 V	I _D = - 3.7 A	-	0.055	0.070		
Forward Transconductanceb	9 _{fs}	V _{DS} = - 15 V, I _D = - 4.9 A		-	9	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		_{GS} = 0 V V _{DS} = - 25 V, f = 1 MHz	-	557			
Output Capacitance	C _{oss}	$V_{GS} = 0 V$ V_{DS}		-	126		pF	
Reverse Transfer Capacitance	C_{rss}			-	90			
Total Gate Charge ^c	Qg			-	15			
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -4.9 \text{ A}$	-	2.1		nC	
Gate-Drain Charge ^c	Q _{gd}			-	3.5	-		
Gate Resistance	R _g		f = 1 MHz		5.26	8.50	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	3			
Rise Time ^c	t _r	V_{DD} = - 15 V, R_L = 6.8 Ω I_D \cong - 1 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	9		ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	20			
Fall Time ^c	t _f			-	9			
Source-Drain Diode Ratings and Chara	acteristics ^b	•						
Pulsed Current ^a	I _{SM}			-	-	- 26	Α	
Forward Voltage	V _{SD}	I _F = - 2 A, V _{GS} = 0 V		-	- 0.8	- 1.2	V	

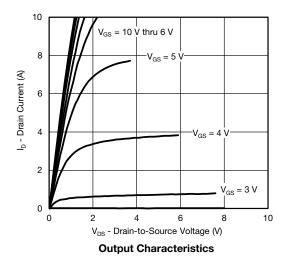
Notes

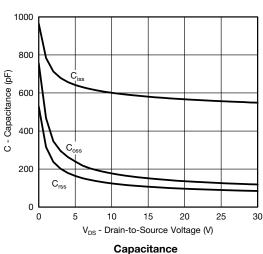
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

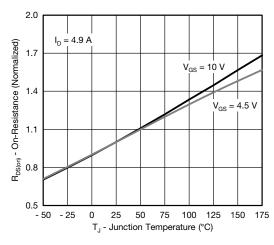
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



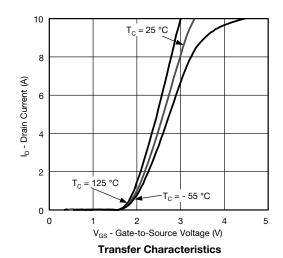
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)

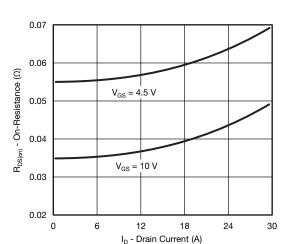




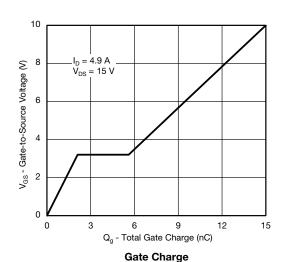


On-Resistance vs. Junction Temperature



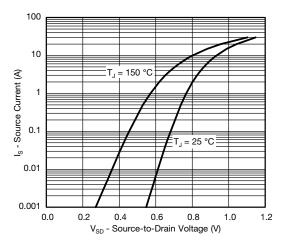


On-Resistance vs. Drain Current

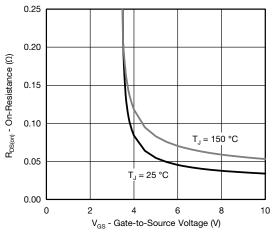




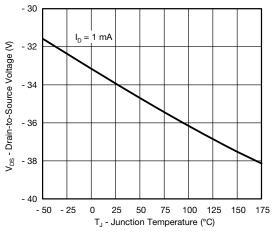
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



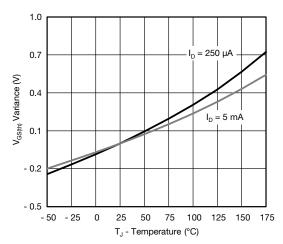
Source Drain Diode Forward Voltage



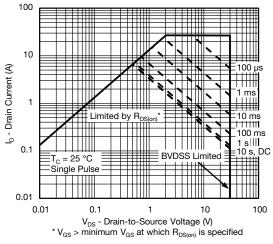
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



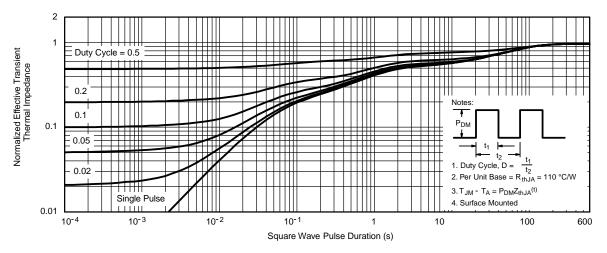
Threshold Voltage



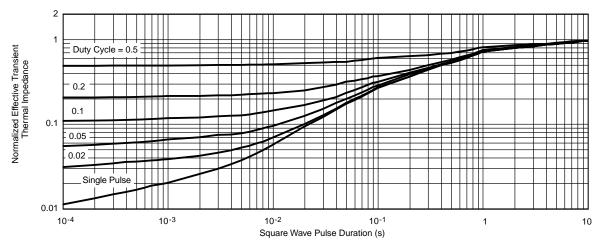
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

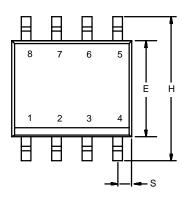
Note

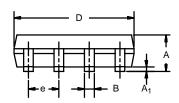
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

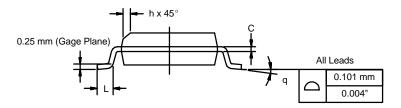
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





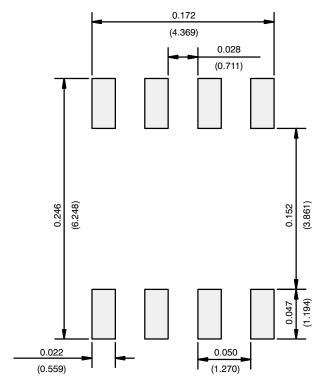


	MILLIMETERS		LLIMETERS INCHES		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Rev I 11-Sep-06					

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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